

2SC2309

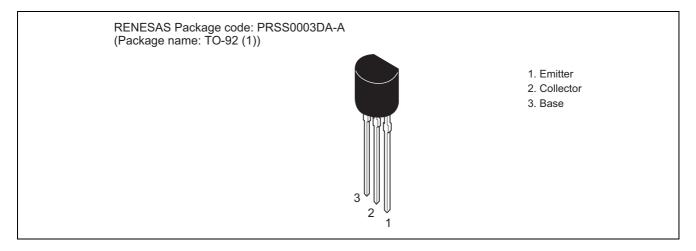
Silicon NPN Epitaxial

REJ03G0696-0200 (Previous ADE-208-1061) Rev.2.00 Aug.10.2005

Application

Low frequency amplifier

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

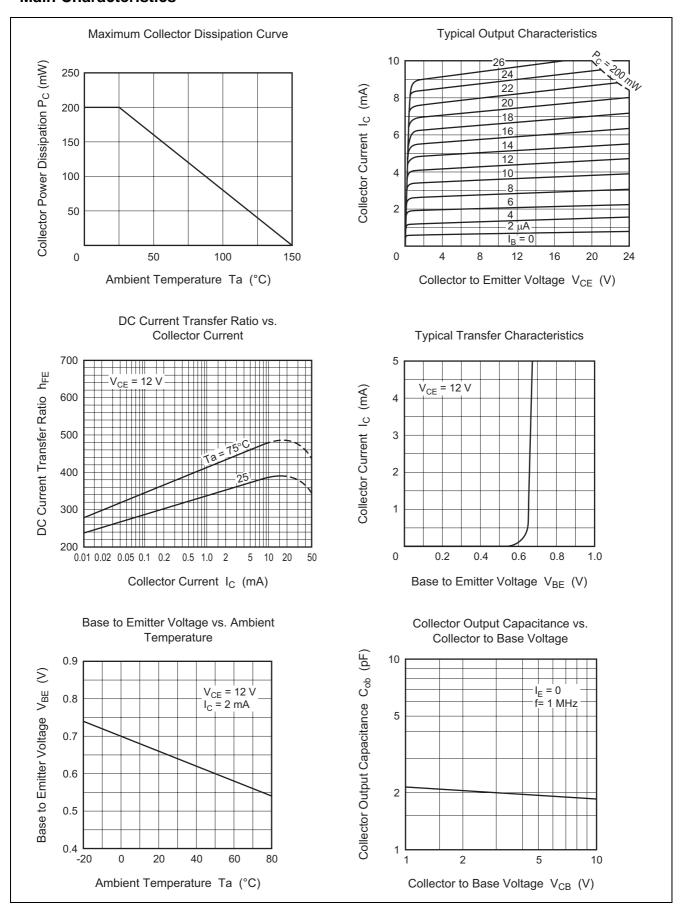
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	55	V
Collector to emitter voltage	V _{CEO}	50	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	Ic	100	mA
Collector power dissipation	Pc	200	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

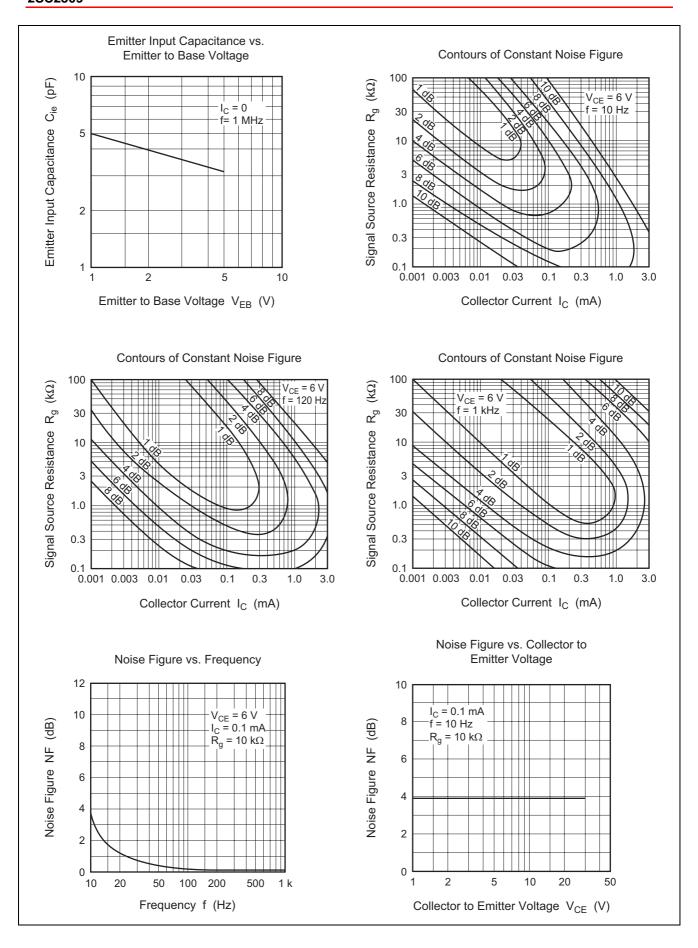
Electrical Characteristics

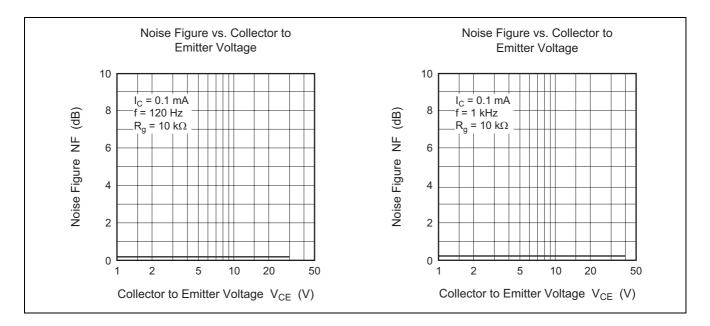
 $(Ta = 25^{\circ}C)$

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	55	_	_	V	$I_C = 10 \ \mu A, \ I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	50	_	_	V	$I_C = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	_	_	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	I _{CBO}	_	_	0.5	μΑ	$V_{CB} = 18 \text{ V}, I_E = 0$
Emitter cutoff current	I _{EBO}	_	_	0.5	μΑ	$V_{EB} = 2 \text{ V}, I_{C} = 0$
DC current transfer ratio	h _{FE}	250	_	500		$V_{CE} = 12 \text{ V}, I_{C} = 2 \text{ mA}$
Base to emitter voltage	V_{BE}	_	_	0.75	V	$V_{CE} = 12 \text{ V}, I_{C} = 2 \text{ mA}$
Collector to emitter saturation voltage	V _{CE(sat)}	_	_	0.2	V	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$
Gain bandwidth product	f⊤	_	230	_	MHz	$V_{CE} = 12 \text{ V}, I_{C} = 2 \text{ mA}$
Collector output capacitance	Cob	_	1.8	3.5	pF	V _{CB} = 10 V, I _E = 0, f = 1 MHz

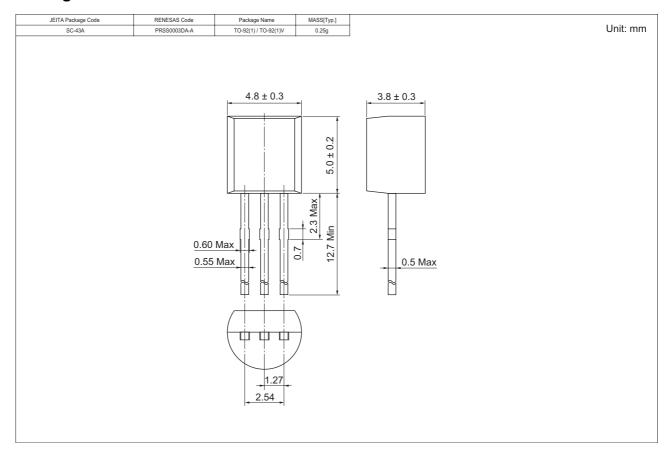
Main Characteristics







Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SC2309DTZ-E	2500	Hold Box, Radial Taping

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